

30V N-Channel MOSFET



SOT-23

Pin Definition:

- 3 1 2
- 1. Gate
- 2. Source
- 3. Drain

PRODUCT SUMMARY

| V _{DS} (V) | $R_{DS(on)}(m\Omega)$ | I _D (A) | |
|---------------------|-----------------------------|--------------------|--|
| 30 | 30 @ V _{GS} = 10V | 5.8 | |
| | 43 @ V _{GS} = 4.5V | 5.0 | |

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

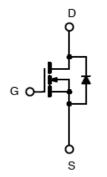
- Load Switch
- PA Switch

Ordering Information

| Part No. | Package | Packing | |
|---------------|---------|-----------------|--|
| TSM3404CX RFG | SOT-23 | 3Kpcs / 7" Reel | |

Note: "G" denotes Halogen Free Product.

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

| Parameter | | Symbol | Limit | Unit | |
|--------------------------------------------------|----------------------------|-----------------------------------|-------------|------|--|
| Drain-Source Voltage | | V _{DS} | 30 | V | |
| Gate-Source Voltage | | V_{GS} | ±20 | V | |
| Continuous Drain Current | | I _D | 5.8 | А | |
| Pulsed Drain Current | | I _{DM} | 20 | А | |
| Continuous Source Current (Diode C | Conduction) ^{a,b} | I _S 2.5 | | А | |
| Maximum Power Dissipation | Ta = 25°C | | 0.75 | W | |
| | Ta = 75°C | P_{D} | 0.48 | | |
| Operating Junction Temperature | | T _J | +150 | °C | |
| Operating Junction and Storage Temperature Range | | T _J , T _{STG} | -55 to +150 | °C | |

Thermal Performance

| Parameter | Symbol | Limit | Unit | | |
|------------------------------------------------------|------------------|-------|------|--|--|
| Junction to Foot Thermal Resistance | $R\Theta_{JF}$ | 75 | °C/W | | |
| Junction to Ambient Thermal Resistance (PCB mounted) | RO _{JA} | 140 | °C/W | | |

Notes

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 10 sec.



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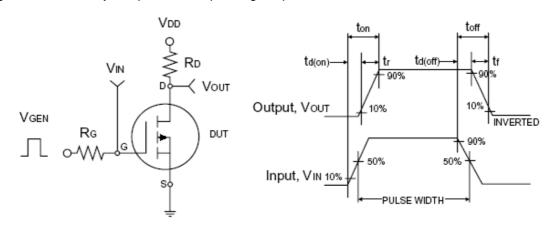


Electrical Specifications (Ta = 25°C unless otherwise noted)

| Parameter | Conditions | Symbol | Min | Тур | Max | Unit |
|----------------------------------|---------------------------------------------------------------------------|---------------------|-----|--------|------|------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{GS} = 0V, I_D = 250\mu A$ | BV _{DSS} | 30 | | 1 | V |
| Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | $V_{GS(TH)}$ | 1 | 1.4 | 3 | V |
| Gate Body Leakage | $V_{GS} = \pm 20V, V_{DS} = 0V$ | I _{GSS} | 1 | | ±100 | μΑ |
| Zero Gate Voltage Drain Current | $V_{DS} = 24V, V_{GS} = 0V$ | I _{DSS} | 1 | | 1.0 | μΑ |
| On-State Drain Current | $V_{DS} = 5V, V_{GS} = 4.5V$ | I _{D(ON)} | 20 | | 1 | Α |
| Danie Course On Otata Basistana | $V_{GS} = 10V, I_D = 5.8A$ | - | | 23 | 30 | |
| Drain-Source On-State Resistance | rain-Source On-State Resistance $V_{GS} = 4.5V$, $I_D = 5A$ $R_{DS(ON)}$ | | 35 | 43 | mΩ | |
| Forward Transconductance | $V_{DS} = 5V, I_{D} = 5A$ | g _{fs} | | 25 | | S |
| Diode Forward Voltage | $I_S = 1.0A, V_{GS} = 0V$ | V _{SD} | | 0.76 | 1 | V |
| Dynamic ^b | | | | | | |
| Total Gate Charge | $V_{DS} = 15V, I_D = 5.8A,$ $V_{GS} = 10V$ | Q_g | - | 4.52 | | |
| Gate-Source Charge | | Q_gs | 1 | 1.24 | 1 | nC |
| Gate-Drain Charge | V _{GS} = 10V | Q_gd | 1 | 1.68 | - | |
| Input Capacitance | 1/ 45)/)/ 0)/ | C _{iss} | - | 400.96 | - | |
| Output Capacitance | $V_{DS} = 15V, V_{GS} = 0V,$ | C _{oss} | 1 | 100.47 | 1 | pF |
| Reverse Transfer Capacitance | f = 1.0MHz | C_{rss} | 1 | 71.82 | 1 | |
| Switching ^c | | | | | | |
| Turn-On Delay Time | 15\(\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ | t _{d(on)} | | 7.42 | | |
| Turn-On Rise Time | $V_{DD} = 15V, R_L = 2.2\Omega,$ | t _r | | 3.41 | | |
| Turn-Off Delay Time | $I_D = 1A, V_{GEN} = 10V,$ | t _{d(off)} | | 20.4 | | nS |
| Turn-Off Fall Time | $R_G = 6\Omega$ | t _f | | 3.01 | | |

Notes:

- a. pulse test: PW \leq 300µS, duty cycle \leq 2% b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

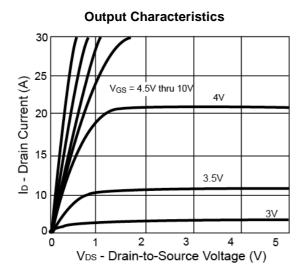
Switchin Waveforms



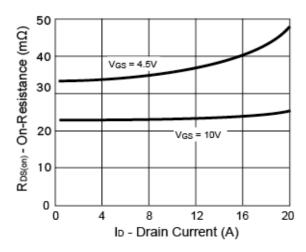
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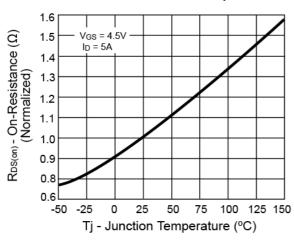
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



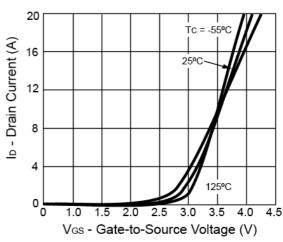
On-Resistance vs. Drain Current



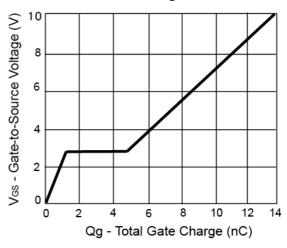
On-Resistance vs. Junction Temperature



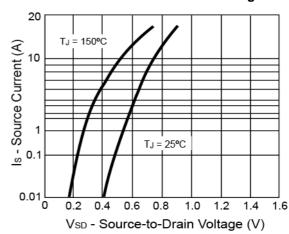
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



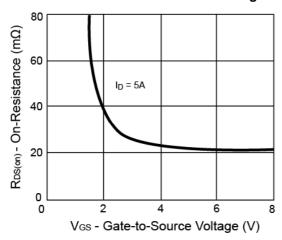


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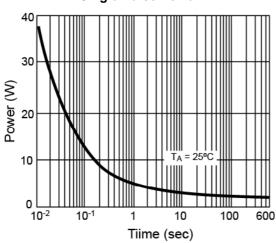
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

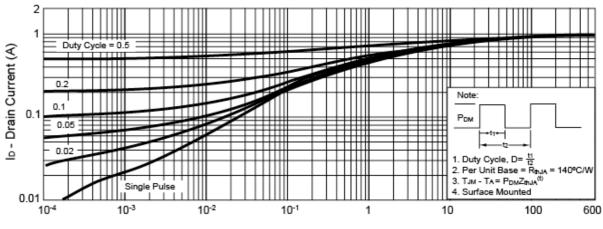


Threshold Voltage 0.2 0.1 Vgs(th) - Variance (V) I_D = 1mA -0.0 -0.1 -0.2 -0.3 -50 -25 25 50 75 100 125 150 Tj - Junction Temperature (°C)

Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



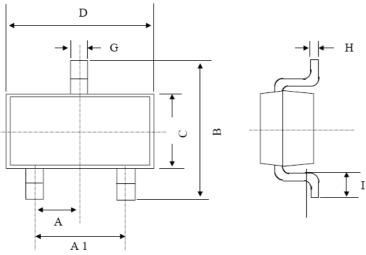
Square Wave Pulse Duration (sec)



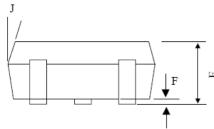
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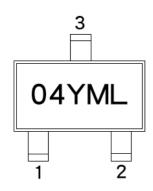
SOT-23 Mechanical Drawing



| OOT OO DIMENIOLONI | | | | | |
|--------------------|-------------|------|--------|-------|--|
| SOT-23 DIMENSION | | | | | |
| DIM | MILLIMETERS | | INCHES | | |
| DIIVI | MIN | MAX | MIN | MAX. | |
| Α | 0.95 | BSC | 0.037 | BSC | |
| A1 | 1.9 | BSC | 0.074 | BSC | |
| В | 2.60 | 3.00 | 0.102 | 0.118 | |
| С | 1.40 | 1.70 | 0.055 | 0.067 | |
| D | 2.80 | 3.10 | 0.110 | 0.122 | |
| E | 1.00 | 1.30 | 0.039 | 0.051 | |
| F | 0.00 | 0.10 | 0.000 | 0.004 | |
| G | 0.35 | 0.50 | 0.014 | 0.020 | |
| Н | 0.10 | 0.20 | 0.004 | 0.008 | |
| Ī | 0.30 | 0.60 | 0.012 | 0.024 | |
| J | 5° | 10° | 5° | 10° | |



Marking Diagram



04 = Device Code

Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S = May T = Jun U = Jul V = Aug

W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code



TSM3404 30V N-Channel MOSFET

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